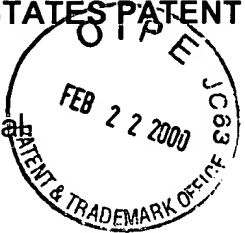


G/P2823

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant: Goldberg, et al  
Serial No.: 09/085,298  
Filing Date: 5/27/98

Art Unit: 2823  
Examiner: Eaton, K.  
Docket No.: TI-25588

#4/B  
Jm  
2-24-00

Title: METHOD FOR THERMAL NITRIDATION AND/OR OXIDATION  
OF SEMICONDUCTOR SURFACE AND RELATED PROCESSING  
EQUIPMENT

Amendment under 37 CFR 1.115

Assistant Commissioner of Patents  
Washington, DC 20231  
February 16, 2000

MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(A)  
I hereby certify that this correspondence is being deposited with  
the U.S. Postal Service as First Class Mail in an envelope addressed  
to: Assistant Commissioner for Patents, Washington, D.C. 20231 on  
2-17-00  
Tommie Chambers  
Tommie Chambers

Dear Sir:

The following amendments and remarks are offered in response to the  
Examiner's Office Action dated 11/17/99. They are respectfully submitted as a  
full and complete response to that Action.

Please amend the above-referenced application as follows:

In the Claims:

Please amend the claims as follows:

4. (amended) The method of claim 1, wherein said silicon-containing structure  
is a silicon substrate and said nitrided portion of said silicon-containing structure  
is a gate dielectric.

Sub  
C2  
B1